

Applicant: Sol P. DiJaili et al.
 Serial No.: 10/789,126
 Filing Date: February 27, 2004
 For: OPTICAL LATCH BASED ON LASING SEMICONDUCTOR OPTICAL AMPLIFIERS

Confirmation No.: 7346
 Atty Docket No.: 15436.247.40.1.1
 Group: 2633

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANTU.S. Patent Documents

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References Cited by Applicants

While the filing of Information Disclosure Statements is voluntary, the procedure is governed by the guidelines of Section 609 of the Manual of Patent Examining Procedure and 37 C.F.R. §§ 1.97 and 1.98. To be considered a proper Information Disclosure Statement, Form PTO-1449 shall be accompanied by a copy of each listed patent or publication or other item of information and a translation of the pertinent portions of foreign documents (if an existing translation is readily available to the applicant), an explanation of relevance of each reference not in the English language, and should be submitted in a timely manner as set out in MPEP Sec. 609.

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